

Product Overview

BD137: 1.5 A, 60 V NPN Power Bipolar Junction Transistor

For complete documentation, see the data sheet.

This series of plastic, medium-power NPN power bipolar junction transistors are designed for use as audio amplifiers and drivers utilizing complementary or quasi complementary circuits.

Features

- Minimum DC Current Gain - $h_{FE} = 40$ @ $I_C = 0.15$ A
- BD135, BD137, BD139 are complementary with BD136, BD138, BD140
- These are Pb-Free Devices

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Polarity	Type	$V_{CE(sat)}$ Max (V)	I_C Cont. (A)	V_{CEO} Min (V)	V_{CBO} (V)	V_{EBO} (V)	$V_{BE(sat)}$ (V)	$V_{BE(on)}$ (V)	h_{FE} Min	h_{FE} Max	f_T Min (MHz)	P_{TM} Max (W)	Pack age Type
BD137G	0.1668	Pb-free Halide free	Active	NPN	General Purpose	0.5	1.5	60	60	5	-	1	40	250	-	12.5	TO-225-3

For more information please contact your local sales support at www.onsemi.com.

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